

**IN THE CLAIMS:**

Please note that all claims currently pending and under consideration in the referenced application are shown below, in clean form, for clarity. **NO AMENDMENT TO THE CLAIMS HAS BEEN MADE HEREIN.**

23. (Previously Amended) An operable gate stack, including a non-crystalline metallic silicide film.

24. (Previously Thrice Amended) An operable gate stack, including an amorphous metallic silicide film wherein said metallic silicide film is substantially devoid of silicon clusters.

25. (Previously Thrice Amended) An operable gate stack on a silicon substrate having a dielectric layer thereover, comprising:

a polysilicon layer disposed over said dielectric layer;  
a non-crystalline metallic silicide film disposed over said polysilicon layer; and  
a dielectric cap on said non-crystalline metallic silicide film.

26. (Previously Twice Amended) A gate stack structure comprising an operable gate stack on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.

27. (Previously Amended) The gate stack structure of claim 26 wherein said operable gate stack includes a non-crystalline metallic silicide film.

28. (Previously Twice Amended) The gate stack structure of claim 26 wherein said operable gate stack includes an amorphous metallic silicide film substantially devoid of silicon clusters.

*and 21*

29. A semiconductor device, comprising at least one gate stack having a non-crystalline metallic silicide film.

30. The semiconductor device of claim 29, wherein said at least one gate stack comprises:  
a silicon substrate having a dielectric layer thereover;  
a polysilicon layer disposed over said dielectric layer;  
a non-crystalline metallic silicide film disposed over said polysilicon layer; and  
a dielectric cap on said non-crystalline metallic silicide film.

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31. A semiconductor device, comprising at least one gate stack structure on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.

32. The semiconductor device of claim 31, wherein said at least one gate stack structure includes a non-crystalline metallic silicide film.

33. The semiconductor device of claim 31, wherein said at least one gate stack structure includes an amorphous silicide film substantially devoid of silicon clusters.